

NTMD6P02, NVMD6P02

MOSFET – Power, Dual, P-Channel, SOIC-8 6 A, 20 V

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Dual SOIC-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Avalanche Energy Specified
- These Devices are Pb-Free and are RoHS Compliant
- NVMD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-20	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	V
Thermal Resistance – Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 70^\circ\text{C}$ Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D P_D I_D I_{DM}	62.5 2.0 -7.8 -5.7 0.5 -3.89 -40	$^\circ\text{C}/\text{W}$ W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 2) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 70^\circ\text{C}$ Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D P_D I_D I_{DM}	98 1.28 -6.2 -4.6 0.3 -3.01 -35	$^\circ\text{C}/\text{W}$ W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 3) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 70^\circ\text{C}$ Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D P_D I_D I_{DM}	166 0.75 -4.8 -3.5 0.2 -2.48 -30	$^\circ\text{C}/\text{W}$ W A A W A A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = -20$ Vdc, $V_{GS} = -5.0$ Vdc, Peak $I_L = -5.0$ Apk, $L = 40$ mH, $R_G = 25 \Omega$)	E_{AS}	500	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided), $t = 10$ seconds.

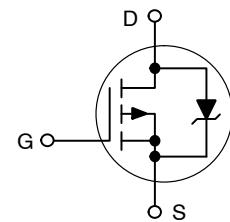


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6 AMPERES, 20 VOLTS

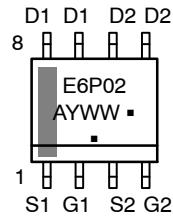
P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



SOIC-8
CASE 751
STYLE 11



E6P02 = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

□ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NVMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

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2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided), t = steady state.
3. Minimum FR-4 or G-10 PCB, t = steady state.
4. Pulse Test: Pulse Width = 300 μ s, Duty Cycle = 2%.

NTMD6P02, NVMD6P02

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)*

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage ($V_{GS} = 0 \text{ Vdc}$, $I_D = -250 \mu\text{A}$)	$V_{(\text{BR})\text{DSS}}$	-20	-	-	Vdc
Temperature Coefficient (Positive)		-	-11.6	-	$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current ($V_{DS} = -20 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $T_J = 25^\circ\text{C}$) ($V_{DS} = -20 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $T_J = 70^\circ\text{C}$)	I_{DSS}	-	-	-1.0 -5.0	μA
Gate-Body Leakage Current ($V_{GS} = -12 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	-100	nA
Gate-Body Leakage Current ($V_{GS} = +12 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	100	nA

ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$)	$V_{GS(\text{th})}$	-0.6	-0.88	-1.20	Vdc
Temperature Coefficient (Negative)		-	2.6	-	$\text{mV}/^\circ\text{C}$
Static Drain-to-Source On-State Resistance ($V_{GS} = -4.5 \text{ Vdc}$, $I_D = -6.2 \text{ A}$) ($V_{GS} = -2.5 \text{ Vdc}$, $I_D = -5.0 \text{ A}$) ($V_{GS} = -2.5 \text{ Vdc}$, $I_D = -3.1 \text{ A}$)	$R_{DS(\text{on})}$	-	0.027 0.038 0.038	0.033 0.050 -	Ω
Forward Transconductance ($V_{DS} = -10 \text{ Vdc}$, $I_D = -6.2 \text{ A}$)	g_{FS}	-	15	-	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = -16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C_{iss}	-	1380	1700	pF
Output Capacitance		C_{oss}	-	515	775	
Reverse Transfer Capacitance		C_{rss}	-	250	450	

SWITCHING CHARACTERISTICS (Notes 5 and 6)

Turn-On Delay Time	$(V_{DD} = -10 \text{ Vdc}, I_D = -1.0 \text{ A}, V_{GS} = -10 \text{ Vdc}, R_G = 6.0 \Omega)$	$t_{\text{d(on)}}$	-	15	25	ns
Rise Time		t_r	-	20	50	
Turn-Off Delay Time		$t_{\text{d(off)}}$	-	85	125	
Fall Time		t_f	-	50	110	
Turn-On Delay Time	$(V_{DD} = -16 \text{ Vdc}, I_D = -6.2 \text{ A}, V_{GS} = -4.5 \text{ Vdc}, R_G = 6.0 \Omega)$	$t_{\text{d(on)}}$	-	17	-	ns
Rise Time		t_r	-	65	-	
Turn-Off Delay Time		$t_{\text{d(off)}}$	-	50	-	
Fall Time		t_f	-	80	-	
Total Gate Charge	$(V_{DS} = -16 \text{ Vdc}, V_{GS} = -4.5 \text{ Vdc}, I_D = -6.2 \text{ A})$	Q_{tot}	-	20	35	nC
Gate-Source Charge		Q_{gs}	-	4.0	-	
Gate-Drain Charge		Q_{gd}	-	8.0	-	

BODY-DRAIN DIODE RATINGS (Note 5)

Diode Forward On-Voltage	$(I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ Vdc})$ $(I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ Vdc}, T_J = 125^\circ\text{C})$	V_{SD}	-	-0.80 -0.65	-1.2	Vdc
Diode Forward On-Voltage	$(I_S = -6.2 \text{ A}, V_{GS} = 0 \text{ Vdc})$ $(I_S = -6.2 \text{ A}, V_{GS} = 0 \text{ Vdc}, T_J = 125^\circ\text{C})$	V_{SD}	-	-0.95 -0.80	-	Vdc
Reverse Recovery Time	$(I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ Vdc}, dI_S/dt = 100 \text{ A}/\mu\text{s})$	t_{rr}	-	50	80	ns
		t_a	-	20	-	
		t_r	-	30	-	
Reverse Recovery Stored Charge		Q_{RR}	-	0.04	-	μC

5. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

6. Switching characteristics are independent of operating junction temperature.

*Handling precautions to protect against electrostatic discharge are mandatory.

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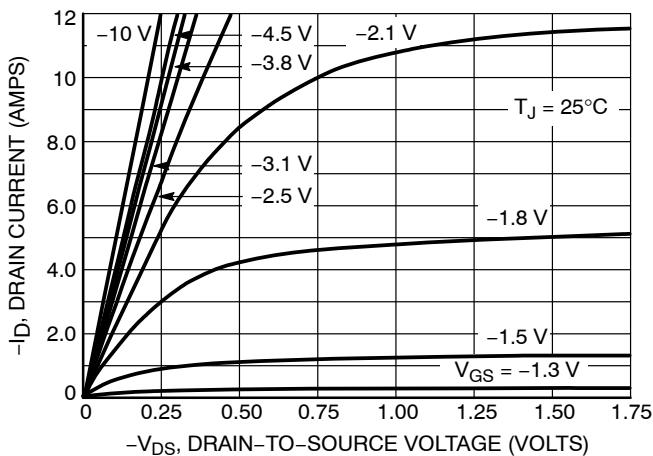


Figure 1. On-Region Characteristics

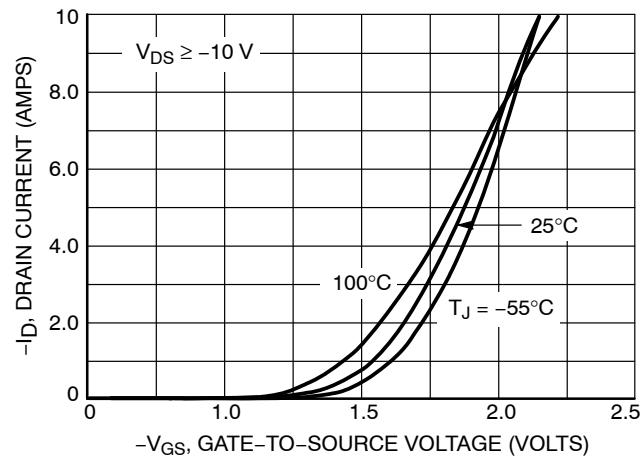


Figure 2. Transfer Characteristics

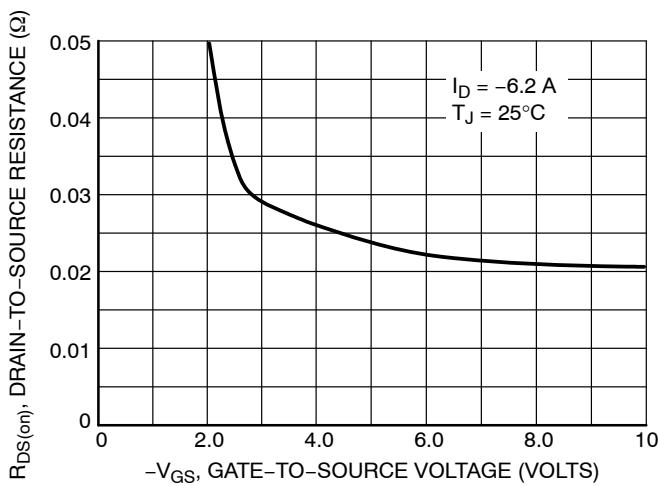


Figure 3. On-Resistance versus Gate-to-Source Voltage

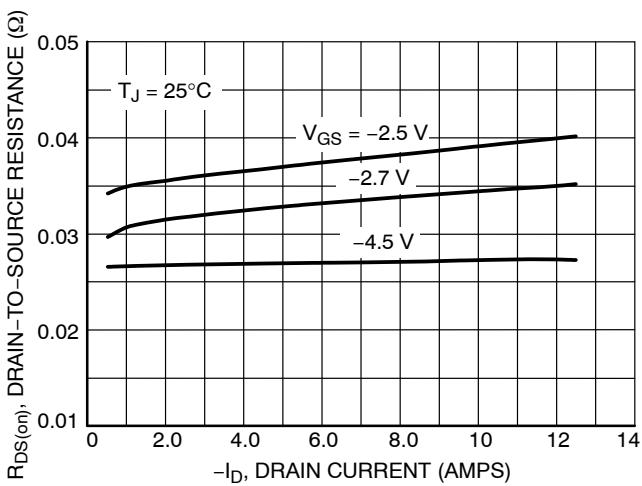


Figure 4. On-Resistance versus Drain Current and Gate Voltage

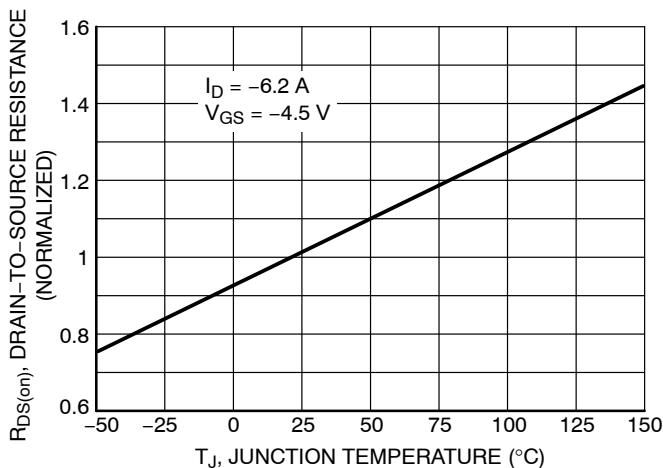


Figure 5. On-Resistance Variation with Temperature

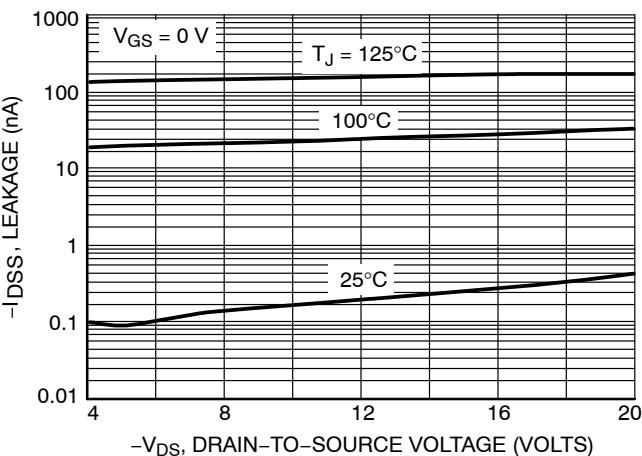
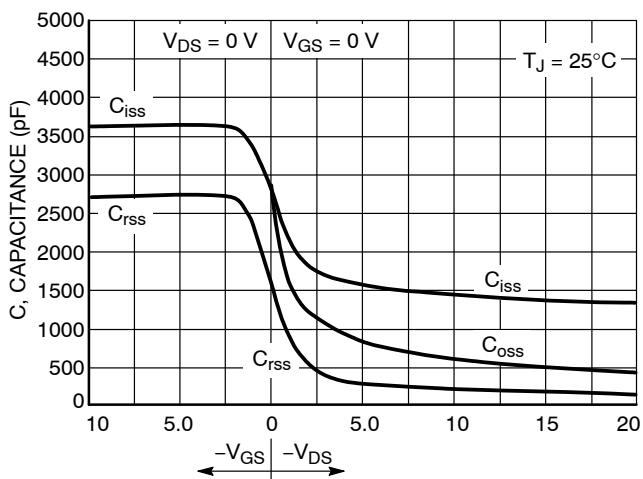


Figure 6. Drain-to-Source Leakage Current versus Voltage

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GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

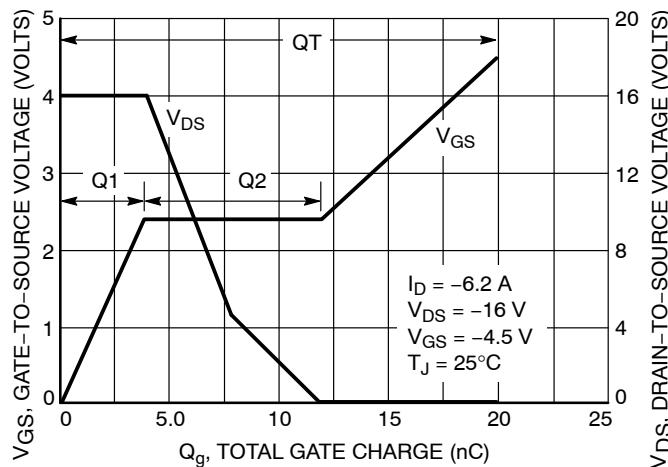


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

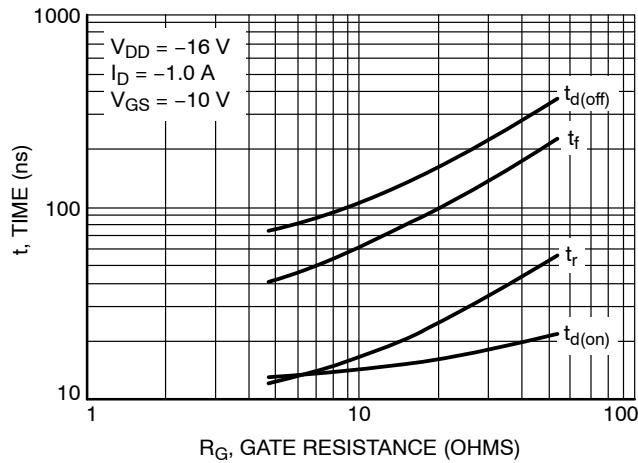


Figure 9. Resistive Switching Time Variation versus Gate Resistance

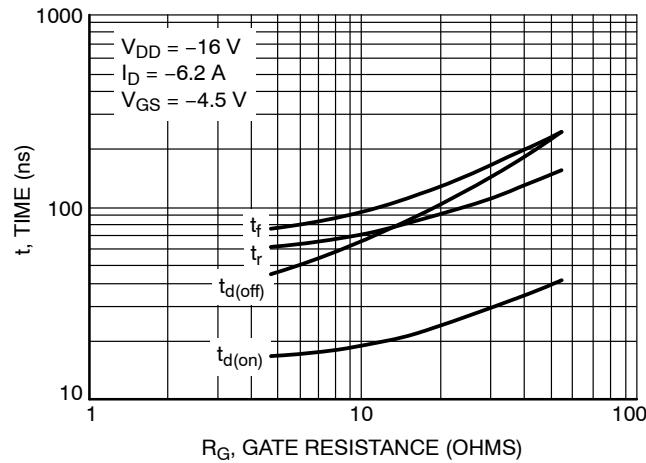


Figure 10. Resistive Switching Time Variation versus Gate Resistance

DRAIN-TO-SOURCE DIODE CHARACTERISTICS

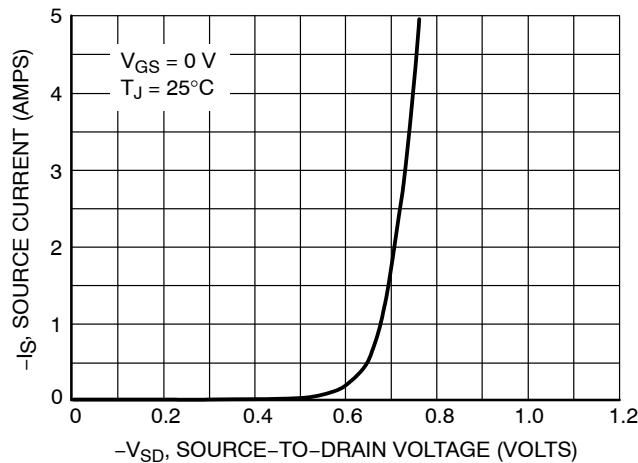


Figure 11. Diode Forward Voltage versus Current

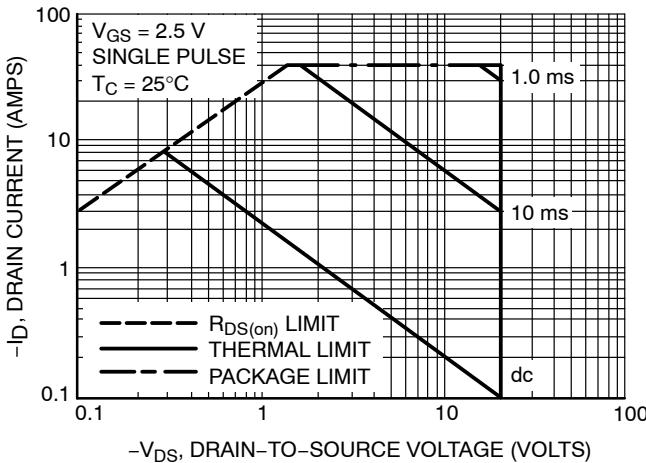


Figure 12. Maximum Rated Forward Biased Safe Operating Area

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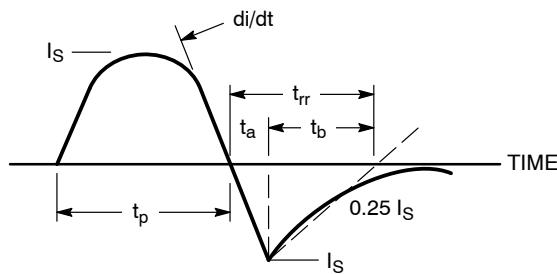


Figure 13. Diode Reverse Recovery Waveform

TYPICAL ELECTRICAL CHARACTERISTICS

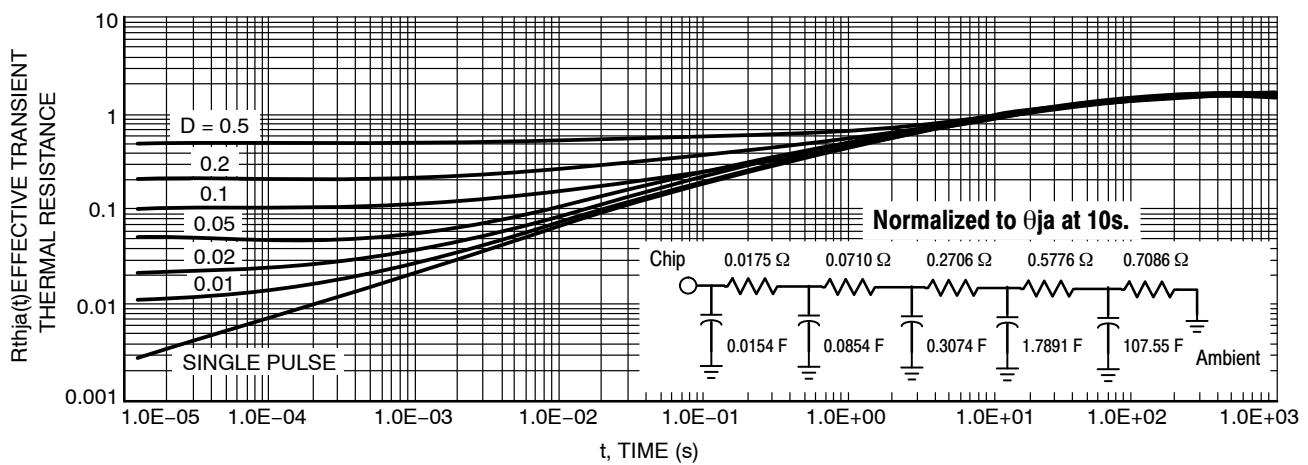


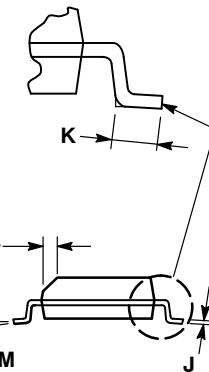
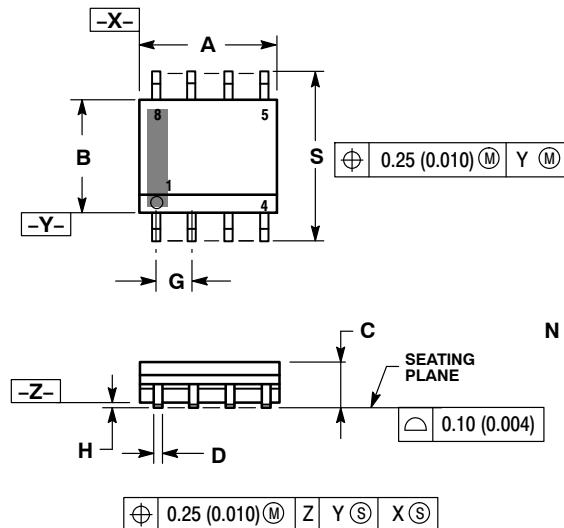
Figure 14. Thermal Response



SCALE 1:1

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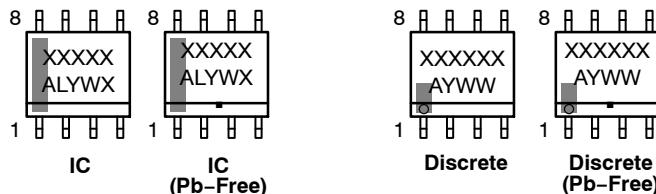
DATE 16 FEB 2011



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*

XXXXXX = Specific Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free Package

XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. Emitter 2. Collector 3. Collector 4. Emitter 5. Emitter 6. Base 7. Base 8. Emitter	STYLE 2: PIN 1. Collector, Die #1 2. Collector, #1 3. Collector, #2 4. Collector, #2 5. Base, #2 6. Emitter, #2 7. Base, #1 8. Emitter, #1	STYLE 3: PIN 1. Drain, Die #1 2. Drain, #1 3. Drain, #2 4. Drain, #2 5. Gate, #2 6. Source, #2 7. Gate, #1 8. Source, #1	STYLE 4: PIN 1. Anode 2. Anode 3. Anode 4. Anode 5. Anode 6. Anode 7. Anode 8. Common Cathode
STYLE 5: PIN 1. Drain 2. Drain 3. Drain 4. Drain 5. Gate 6. Gate 7. Source 8. Source	STYLE 6: PIN 1. Source 2. Drain 3. Drain 4. Source 5. Source 6. Gate 7. Gate 8. Source	STYLE 7: PIN 1. Input 2. External Bypass 3. Third Stage Source 4. Ground 5. Drain 6. Gate 3 7. Second Stage Vd 8. First Stage Vd	STYLE 8: PIN 1. Collector, Die #1 2. Base, #1 3. Base, #2 4. Collector, #2 5. Collector, #2 6. Emitter, #2 7. Emitter, #1 8. Collector, #1
STYLE 9: PIN 1. Emitter, Common 2. Collector, Die #1 3. Collector, Die #2 4. Emitter, Common 5. Emitter, Common 6. Base, Die #2 7. Base, Die #1 8. Emitter, Common	STYLE 10: PIN 1. Ground 2. Bias 1 3. Output 4. Ground 5. Ground 6. Bias 2 7. Input 8. Ground	STYLE 11: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Drain 2 7. Drain 1 8. Drain 1	STYLE 12: PIN 1. Source 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 13: PIN 1. N.C. 2. Source 3. Source 4. Gate 5. Drain 6. Drain 7. Drain 8. Drain	STYLE 14: PIN 1. N-Source 2. N-Gate 3. P-Source 4. P-Gate 5. P-Drain 6. P-Drain 7. N-Drain 8. N-Drain	STYLE 15: PIN 1. Anode 1 2. Anode 1 3. Anode 1 4. Anode 1 5. Cathode, Common 6. Cathode, Common 7. Cathode, Common 8. Cathode, Common	STYLE 16: PIN 1. Emitter, Die #1 2. Base, Die #1 3. Emitter, Die #2 4. Base, Die #2 5. Collector, Die #2 6. Collector, Die #2 7. Collector, Die #1 8. Collector, Die #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. Anode 2. Anode 3. Source 4. Gate 5. Drain 6. Drain 7. Cathode 8. Cathode	STYLE 19: PIN 1. Source 1 2. Gate 1 3. Source 2 4. Gate 2 5. Drain 2 6. Mirror 2 7. Drain 1 8. Mirror 1	STYLE 20: PIN 1. Source (N) 2. Gate (N) 3. Source (P) 4. Gate (P) 5. Drain 6. Drain 7. Drain 8. Drain
STYLE 21: PIN 1. Cathode 1 2. Cathode 2 3. Cathode 3 4. Cathode 4 5. Cathode 5 6. Common Anode 7. Common Anode 8. Cathode 6	STYLE 22: PIN 1. I/O Line 1 2. Common Cathode/VCC 3. Common Cathode/VCC 4. I/O Line 3 5. Common Anode/GND 6. I/O Line 4 7. I/O Line 5 8. Common Anode/GND	STYLE 23: PIN 1. Line 1 IN 2. Common Anode/GND 3. Common Anode/GND 4. Line 2 IN 5. Line 2 OUT 6. Common Anode/GND 7. Common Anode/GND 8. Line 1 OUT	STYLE 24: PIN 1. Base 2. Emitter 3. Collector/Anode 4. Collector/Anode 5. Cathode 6. Cathode 7. Collector/Anode 8. Collector/Anode
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. Enable 4. ILIMIT 5. Source 6. Source 7. Source 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBUCK 7. VBUCK 8. VIN
STYLE 29: PIN 1. Base, Die #1 2. Emitter, #1 3. Base, #2 4. Emitter, #2 5. Collector, #2 6. Collector, #2 7. Collector, #1 8. Collector, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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